

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBU0240 (Lead-free Device)

Io = 200 mA

VR = 40 Volts



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Majority carrier conduction.

Mechanical data

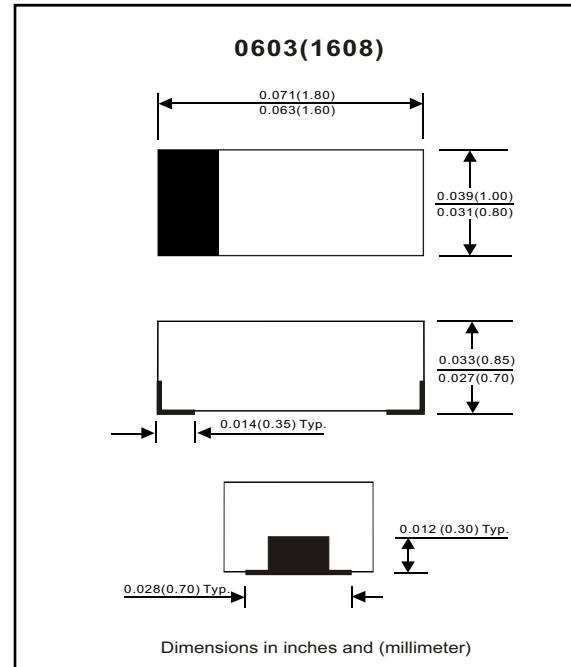
Case: 0603(1608) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM}			45	V
Reverse voltage		V _R			40	V
Average forward current		I _o			200	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I _{FSM}		2000		mA
Power Dissipation		P _D			150	mW
Sunction temperature		T _{TSG}	-40		+125	°C
Junction temperature		T _j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 200 mA DC	V _F		0.45	0.55	V
Reverse current	V _R = 30V	I _R		1	10	uA
Capacitance between terminals	F = 1 MHZ and 10 VDC reverse voltage	C _T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBU0240)

Fig. 1 - Forward characteristics

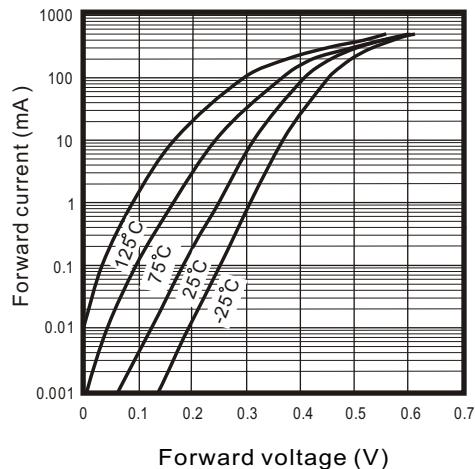


Fig. 2 - Reverse characteristics

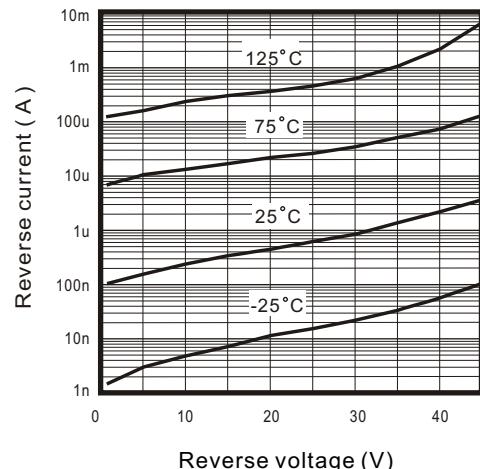


Fig. 3 - Capacitance between terminals characteristics

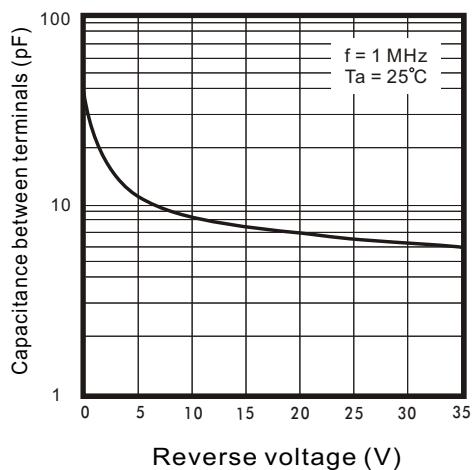


Fig. 4 - Current derating curve

